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(54) Title: SEMICONDUCTOR LIGHT EMITTING DEVICE, LIGHT EMITTING MODULE, LIGHTING APPARATUS, DISPLAY ELEMENT AND MANUFACTURING METHOD OF SEMICONDUCTOR LIGHT EMITTING DEVICE

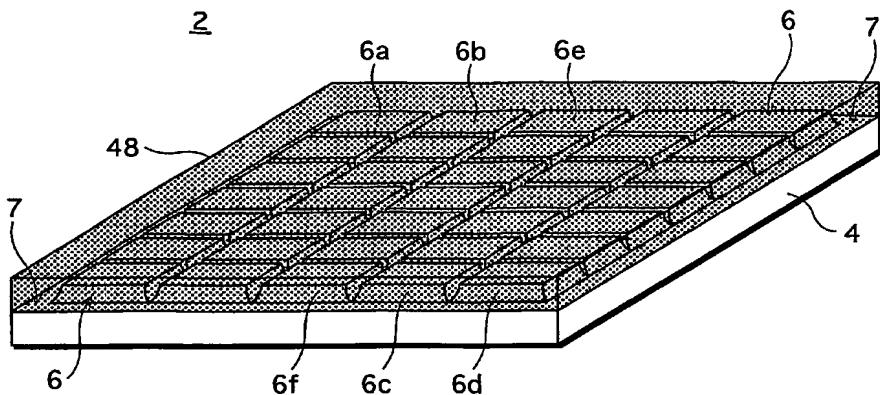
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(57) Abstract: An LED array chip (2), which is one type of a semiconductor light emitting device, includes an array of LEDs (6), a base substrate (4) supporting the array of the LEDs (6), and a phosphor film (48). The array of LEDs (6) is formed by dividing a multilayer epitaxial structure including a light emitting layer into a plurality of portions. The phosphor film (48) covers an upper surface of the array of the LEDs (6) and a part of every side surface of the array of LEDs (6). Here, the part extends from the upper surface to the light emitting layer.

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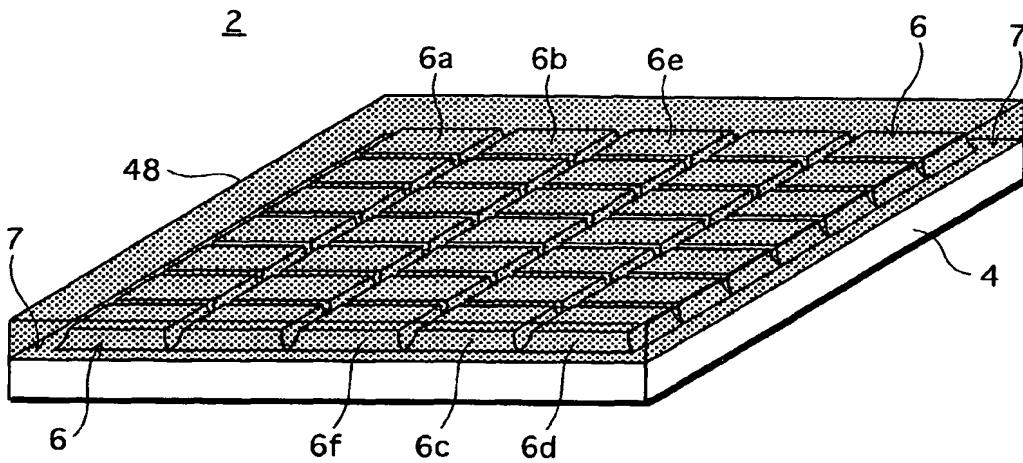
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